


# **ZEP520**

**ZEONREXElectronicChemicals**

**HighResolutionPositive  
ElectronBeamResist**



# **ZEP520**

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Anyprocessconditionsanddataareexamples.  
Thosewillnotguaranteethesamedataincustomers' process.

## 1.Characteristics

ZEP520 series are high performance positive EB resists which show high resolution, high sensitivity and high dry etch resistance.

They are suitable for various EB processes.

### (1)Resolution

Show high resolution and rectangle pattern profile

### (2)Resistant to dry etching

Show high dry etch resistance and are almost equivalent to that of positive photoresists generally used

### (3)Sensitivity

Show high sensitivity

## 2.Properties

Item	Mw	Viscosity (mPa*s)	Solvent	Form
ZEP520-12	57,000	12	o-Dichlorobenzene	1QT bottle or 100ml bottle
ZEP520		22		
ZEP520A		7	Anisole	
ZEP520A		11		

## 3.Thinner

Item	Composition	Remarks	Form
ZEP-S	o-Dichlorobenzene	ZEP520-12	1QT bottle
		ZEP520	
ZEP-A	Anisole	ZEP520A	
		ZEP520A	

## 4.Developer

Item	Composition	Remarks	Form
ZEP-RD	Xylene(o-,m-,p- mixed)	standard	1GL bottle
ZEP-N50	n-Amylacetate	high resolution	
ZED-WN	o-Xylene	high resolution	
ZEP-SD	2-Butanone 40% Methylisobutylketone 60%	high sensitivity	

## 5.Rinse

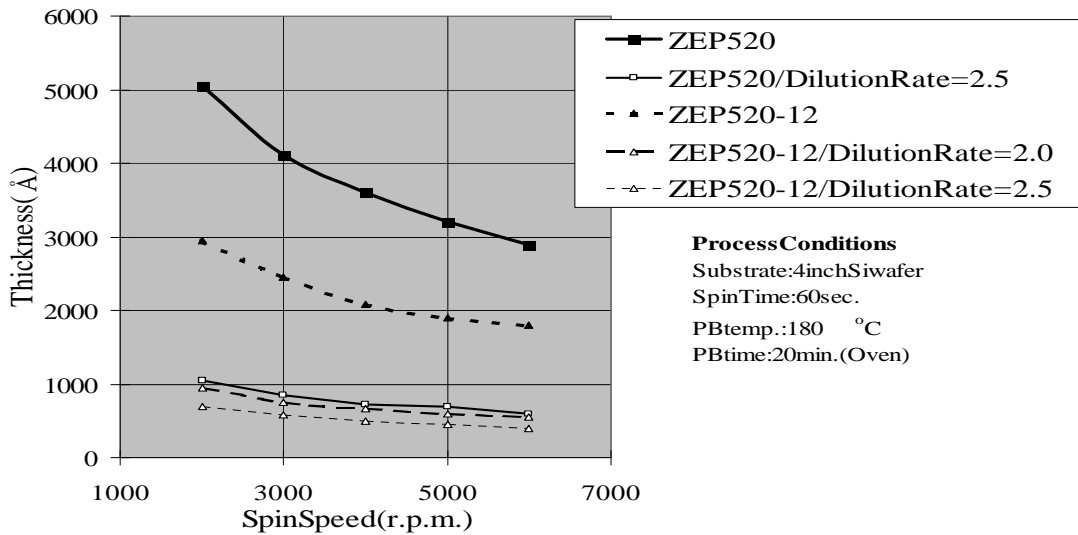
Item	Composition	Remarks	Form
ZMD-B	Methylisobutylketone 89% Isopropylalcohol 11%		1GLbottle

## 6.Remover

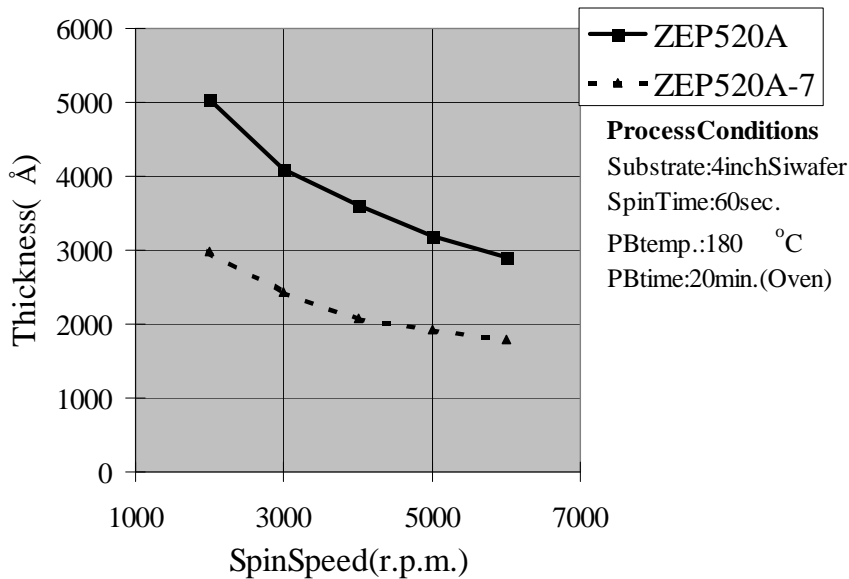
Item	Composition	Remarks	Form
ZDMAC	Dimethylacetamide		1GLbottle

## 7.SpinCurve

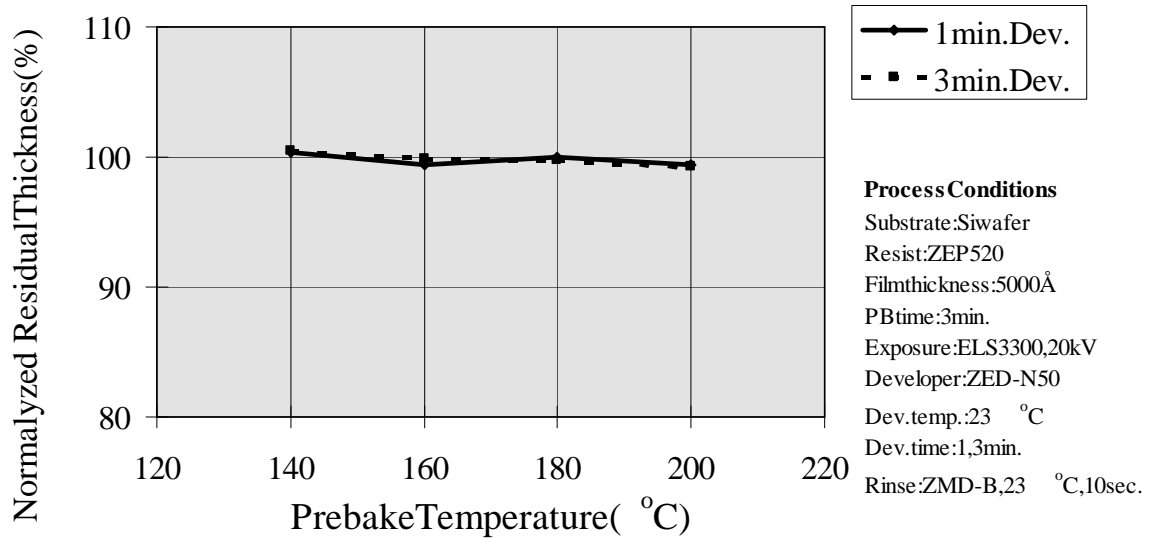
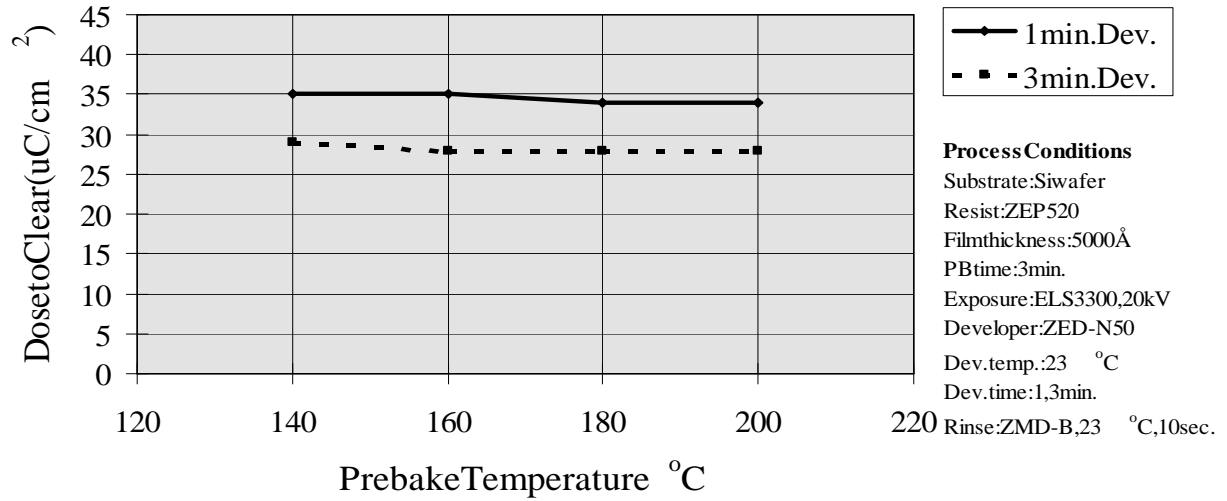
### ZEP520SpinCurve



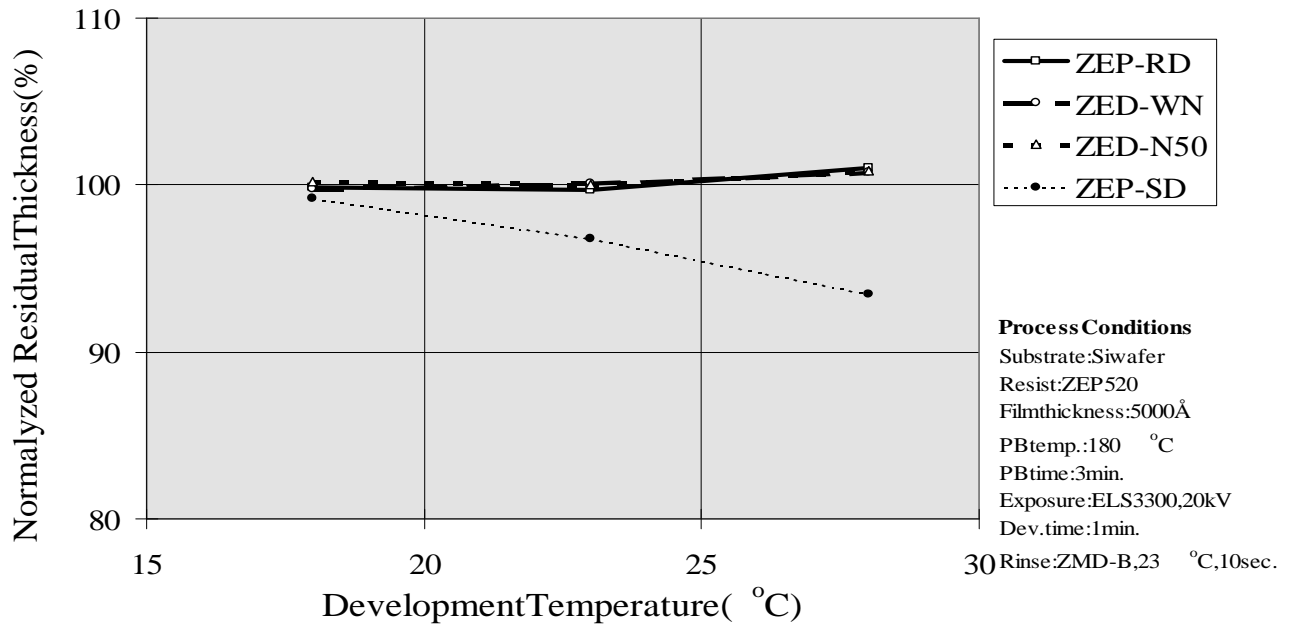
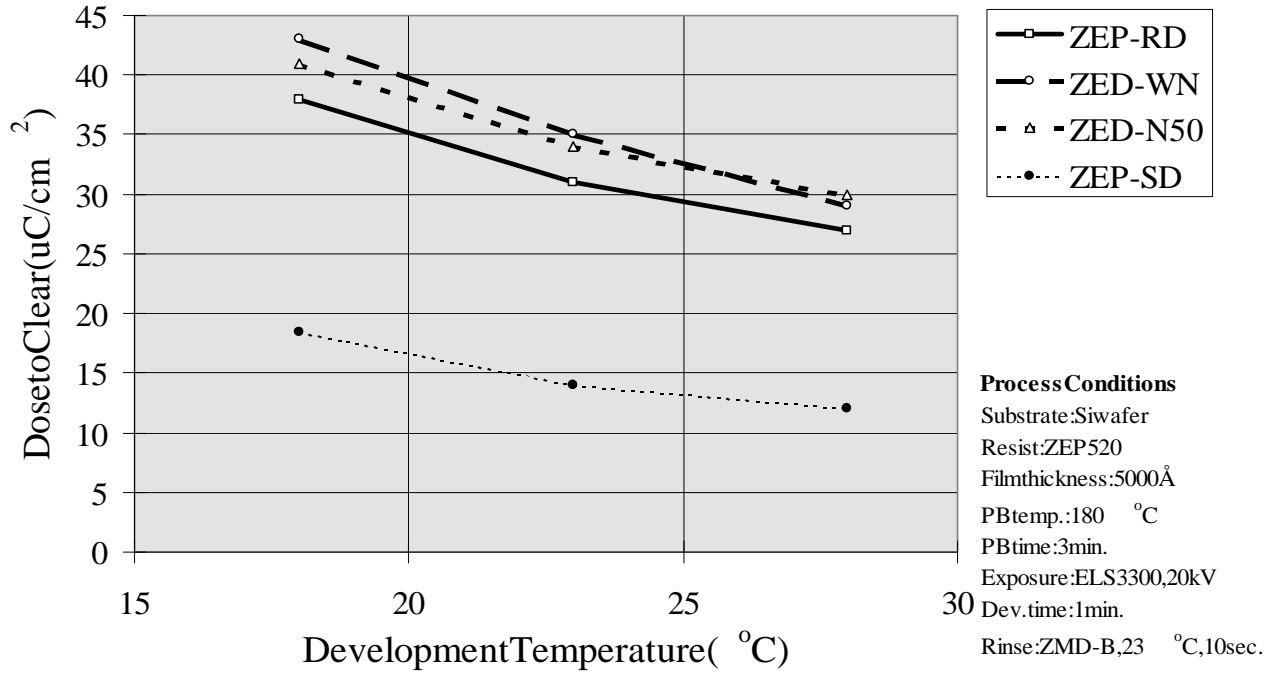
### ZEP520ASpinCurve



## 8. Dependence on Pre-bake Temperature

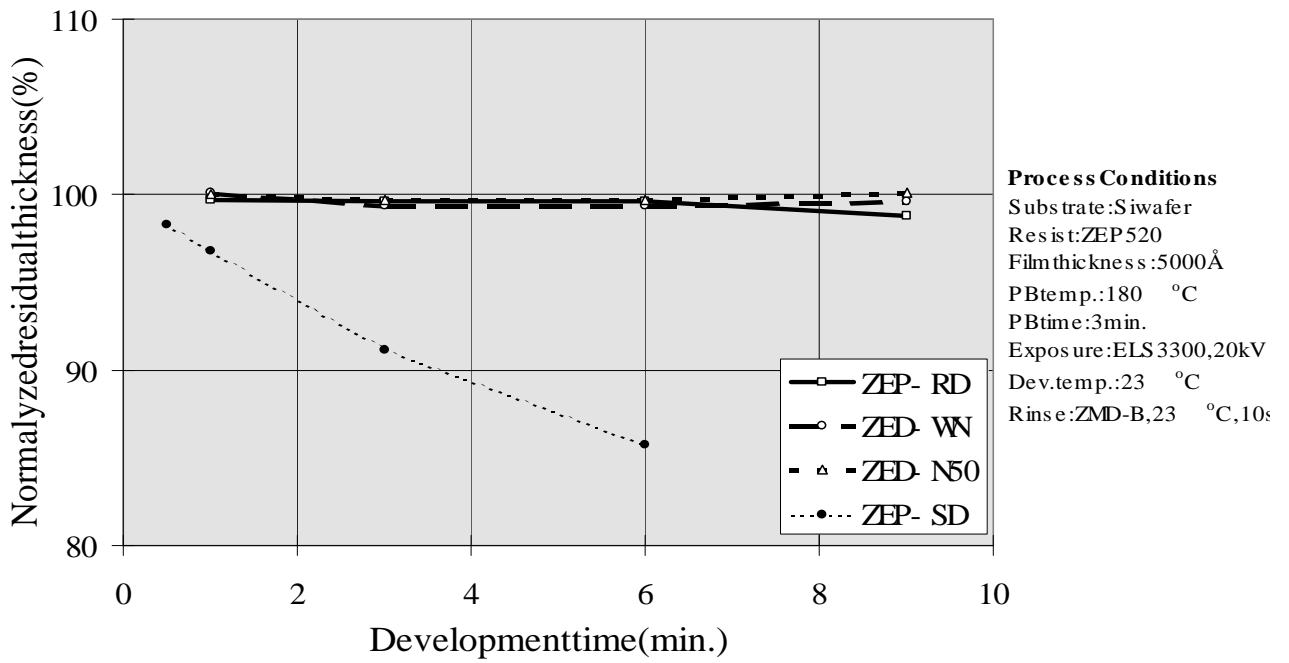
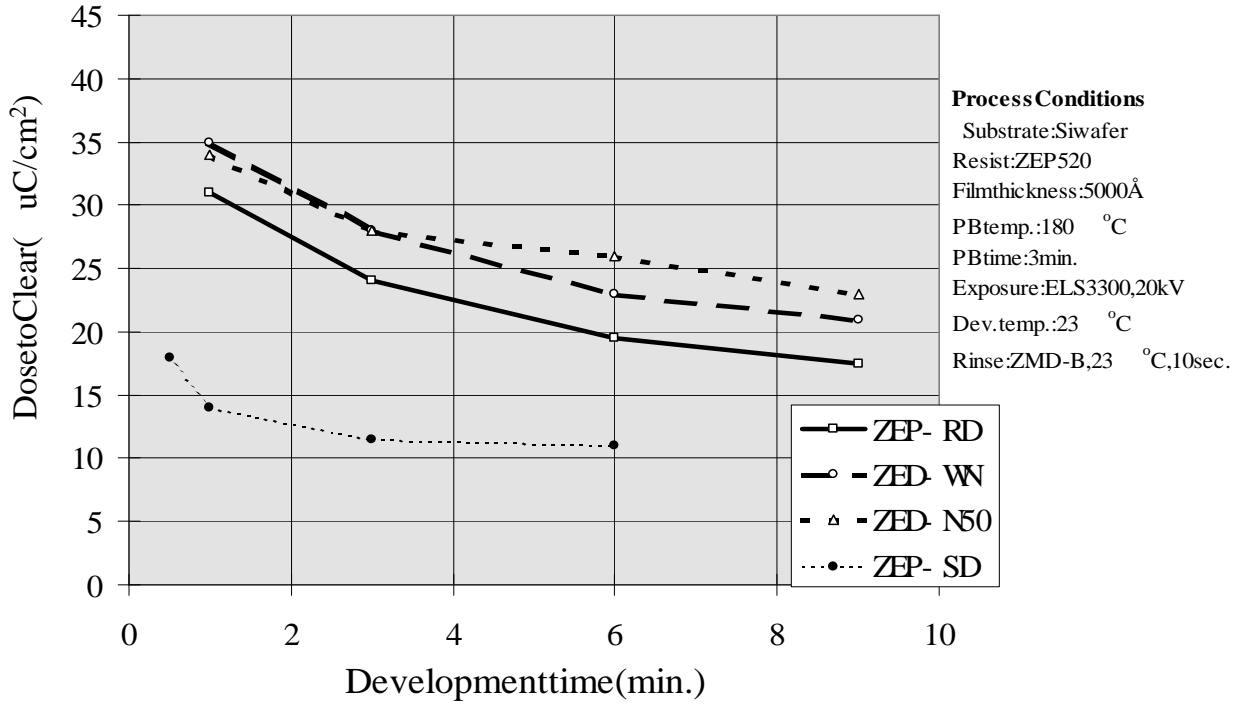


## 9. Dependence on Development Temperature

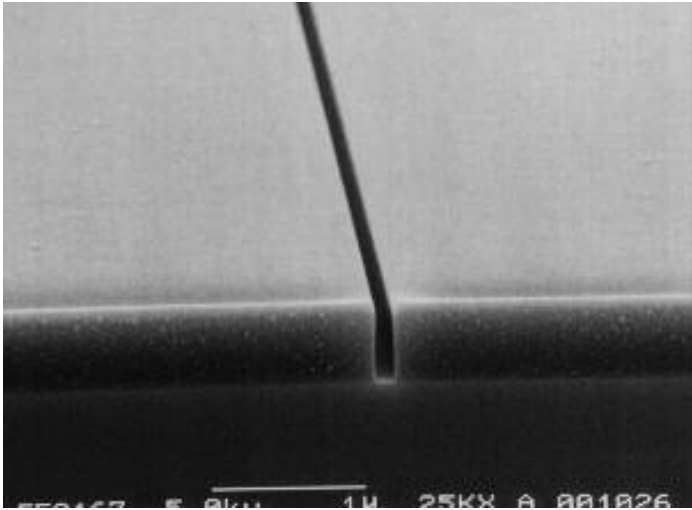


# 9. Dependence on Development Time

A



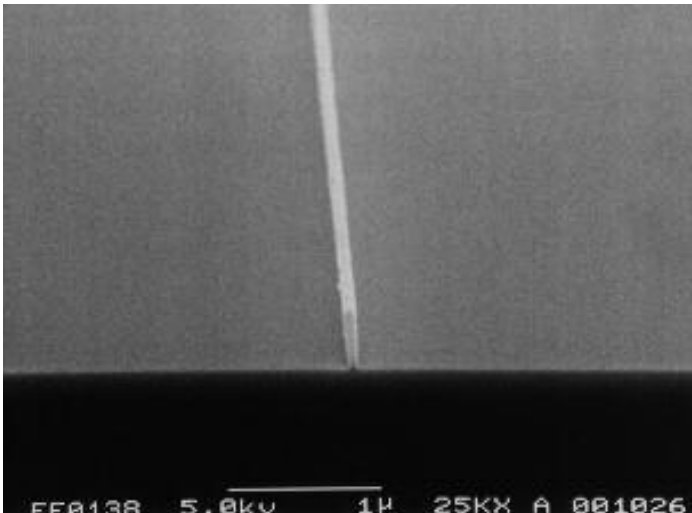
## 10. Application Examples



### 0.15 $\mu\text{m}$ Isolated Space

#### Process Conditions

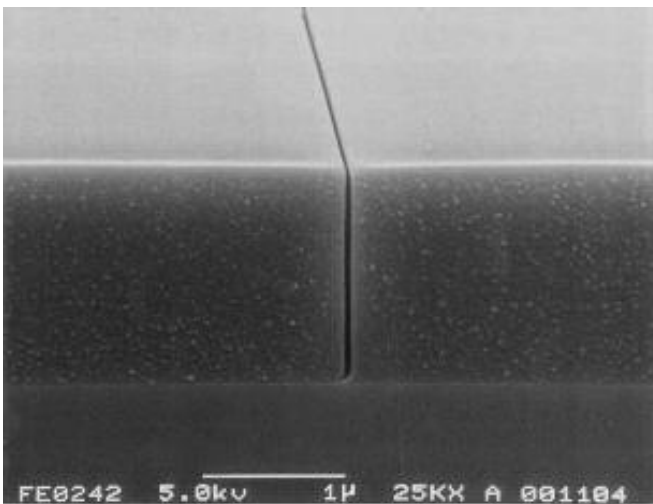
Resist: ZEP520  
Film thickness: 5000 Å  
PB temp.: 180 °C  
PB time: 2 min.  
Exposure: 30kV,  $5 \times 10^{-11}$  A, 1 line exp.  
 $50 \times 10^{-5} \mu\text{C/cm}$   
Dev. temp.: ZED -WN, 23 °C, 30 sec.  
Rinse: IPA, 23 °C, 20 sec.



### 0.1 $\mu\text{m}$ Isolated Line

#### Process Conditions

Resist: ZEP520  
Film thickness: 5000 Å  
PB temp.: 180 °C  
PB time: 2 min.  
Exposure area: 100  $\mu\text{m}$  (20000  $\times$  20000 dot)  
Exposure: 30kV,  $5 \times 10^{-11}$  A, 1 line exp.  
0.7  $\mu\text{sec./dot}$   
Dev. temp.: ZED -WN, 23 °C, 60 sec.  
Rinse: IPA, 23 °C, 20 sec.



### 0.05 $\mu\text{m}$ Isolated Space

#### Process Conditions

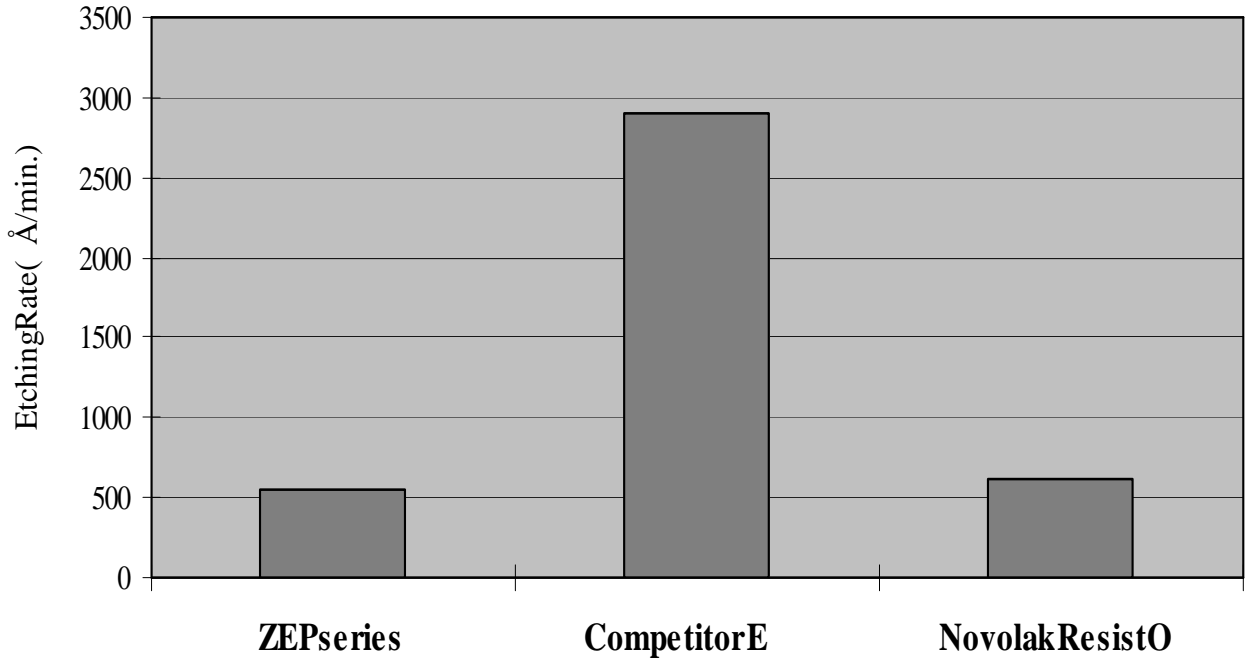
Resist: ZEP520  
Film thickness: 15000 Å  
Exposure: 75kV



# 11. Dry Etching Resistance

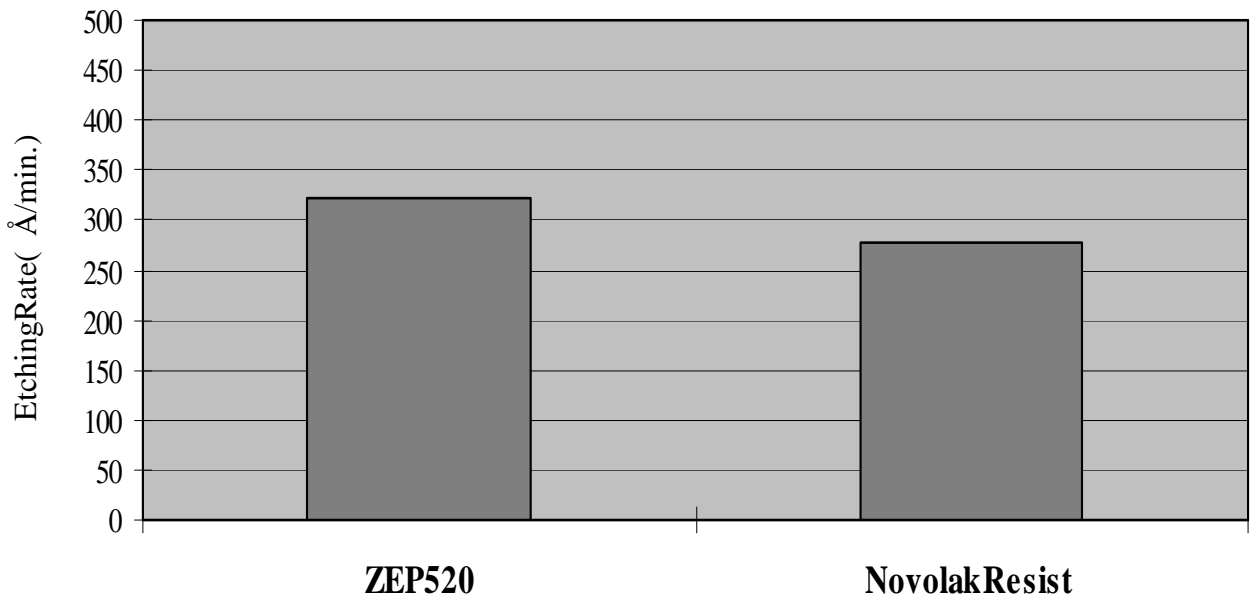
## (1) CF<sub>4</sub> Dry Etching Rate

CF<sub>4</sub> Dry Etching Conditions  
0.15 torr, 70 sccm, 200W



## (2) Cl<sub>2</sub>+O<sub>2</sub> Dry Etching Rate

Cl<sub>2</sub>+O<sub>2</sub> Dry Etching Conditions  
Cl<sub>2</sub>/O<sub>2</sub>=4/1, 5min.



## 12.ExampleofProcessConditions

(1)Coating	ZEP520/520A2000rpm ×60sec → 5000Å ZEP520-12/520A-72000rpm ×60sec → 3000Å
(2)Pre -bake	170-200°C×20-30min.(Oven) 170-200°C×2-5min.(HotPlate)
(3)Exposure	20-50μC/cm <sup>2</sup> at20kV
(4)Development	20-25°C×60-360sec.(Dipping) ZEP-RD,ZED -N50,ZED -WN
(5)Rinse	20-25°C×10-60sec.(Dipping) ZMD-B
(6)Postbake	Incaseofwetetching 100-140°C×20-30min.(Oven) 100-140×2-3min.(HotPlate)
(7)De -scum	O <sub>2</sub> -plasma
(8)Etching	Dryprocessandwetprocesscanbeused.  <u>WetEtchingsolutionforCr</u> Ammoniumcerium(IV)nitrate (NH <sub>4</sub> ) <sub>2</sub> Ce(NO <sub>3</sub> ) <sub>6</sub> 13-18wt% Perchloricacid HClO <sub>4</sub> 3-8wt% Purewater H <sub>2</sub> O 77-84wt%
(9)Resist Removing	<deep -UV+organicsolvent > 1 <sup>st</sup> step:185nm+254nm,10mW/cm <sup>2</sup> ,3min.-irradiation 2 <sup>nd</sup> step: Dimethylacetamide(DMAC)or1 -Methyl-2-pyrrolidinone(NMP), 23°C×1min. *AsthepolymerofZEP520isdecomposedbydeep -UVirradiation, itcanbe easilyremoved.  <organicsolvent> N-methyl-2-pyrrolidone(30 -35°C)  <hotH <sub>2</sub> SO <sub>4</sub> -H <sub>2</sub> O <sub>2</sub> > hotH <sub>2</sub> SO <sub>4</sub> -H <sub>2</sub> O <sub>2</sub> (90-100°C)

## 13. Handling Precautions

- (1) Flammable Liquid
- (2) Harmful by inhalation
- (3) Avoid contact with skin and eyes

**CAUTION:** Open carefully. Use in well ventilated area. In case of contact with skin and eyes, rinse immediately with plenty of water for 15 minutes and get medical attention. In case of fire use Alcohol form CO<sub>2</sub> or dry chemical, never use water.

**STORAGE:** Keep capped and away from oxidants, sparks and open flame. Store at cool [32 °F (0 °C) - 77 °F (25 °C)], dark place. Use in clean room.

## 14. Appendix

### (1) Refractive Index of ZEP520 Film

#### Cauchy Coefficient

$$n = n_0 + n_1/\lambda^2 + n_2/\lambda^4$$

$$n_0 = 1.541093$$

$$n_1 = 4.113002 \times 10^5$$

$$n_2 = 4.070357 \times 10^{12}$$

$$\text{Absorption coefficient} = 0$$

Unit of  $\lambda$  : Å

Measured by UV -1250/SE (KLA Tencor)

### (2) Glass Transition Temperature of ZEP520 Polymer

T<sub>g</sub>: 105 °C Measured by DSC

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